

इंडियन इंस्टीट्यूट ऑफ टेक्नोलॉजी दिल्ली
हौज खास, नई दिल्ली -110016
(औद्योगिक अनुसंधान एवं विकास इकाई)
INDIAN INSTITUTE OF TECHNOLOGY DELHI
Hauz Khas, New Delhi-110016
(Industrial Research & Development Unit)

No. IITD/IRD/RM00119G/ 24441

Dated: 27/05/2026

Advertisement No.: IITD/IRD/128/2026

Applications from Indian nationals are invited for project appointment under the following project. Appointment shall be on contractual basis with consolidated pay, renewable yearly or upto the duration of the project, whichever is earlier. निम्नलिखित परियोजना के तहत भारतीय नागरिकों से आवेदन आमंत्रित किए जाते हैं। अपॉइंटमेंट, अनुबंधित आधार पर समेकित वेतन, नवीकरणीय वार्षिक या परियोजना की अवधि तक, जो भी पहले हो, के साथ होगा।

Title of the Project	Design and Measurement of InP-based HEMT devices for THz applications.(RM00119G)	
Funding Agency	DEPARTMENT OF DEFENCE RESEARCH & DEVELOPMENT ORGANISATION, MINISTRY OF DEFENCE	
Name of the Project Investigator	Prof. Rahul Mishra [email ID: ramis@care.iitd.ac.in]	
Deptt./Centre	Centre for Applied Research in Electronics (CARE)	
Duration of the Project	Upto: 28/03/2029	
Post (s)	Consolidated fellowship / Pay-slab	Qualifications
Research Associate (a) - 01	Rs.58,000/-p.m. plus HRA @27%	Essential: PhD in Electronics, physics or related area. Experience in semiconductor/nanoelectronic device design, fabrication or characterization. Desirable: Experience in InP/GaN/GaAs HEMTs, TCAD tools, thin-film deposition, nanofabrication. Role: Lead the project team and coordinate device design, fabrication-related activities, measurements, data analysis, reporting and collaborator interactions.
Research Associate (b) - 01	Rs.58,000/-p.m. plus HRA @27%	Essential: 1 st class M.Tech./MS with 03 years research experience or PhD in electronics, physics or related area with experience in semiconductor device physics and simulation. Desirable: Experience with TCAD tools such as Silvaco, Synopsys Sentaurus, or equivalent. Prior work on III-V semiconductor devices such as InP/GaN/GaAs HEMTs will be preferred. Role: TCAD-based design and optimization of InP HEMT multilayer epilayer structures and device geometry, including

The posts may be downgraded as per discretion of the Selection Committee if none of the candidate is found suitable for the post.

The candidates who are interested to apply for the above post should download **Form No. IRD/REC-4** from the IRD Website (<http://ird.iitd.ac.in/rec>) of IIT Delhi and submit the duly filled form with complete information regarding educational qualifications indicating percentage of marks/division, details of work experience etc. **by e-mail with advertisement No. on the subject line to Prof. Rahul Mishra at email id: ramis@iitd.ac.in**

IIT Delhi reserves the right to fix higher criteria for short-listing of eligible candidates from those satisfying advertised qualification and requirement of the project post and their name will be displayed on web link (<http://ird.iitd.ac.in/shortlisted>) alongwith the online interview details. Only short-listed candidates will be informed for online interview. In case any clarification is required on eligibility regarding the above post, the candidate may contact **Prof. Rahul Mishra at email id: ramis@care.iitd.ac.in**

5% relaxation of marks may be granted to the SC/ST Candidates. In case of selection of a retired/superannuated government employee, his/her salary will be fixed as per prevailing IRD norms. अनुसूचित जाति / अनुसूचित जनजाति के उम्मीदवारों को अंकों की 5% छूट दी जा सकती है। एक सेवानिवृत्त सरकारी कर्मचारी के चयन के मामले में उसका वेतन वर्तमान आईआरडी मानदंडों के अनुसार तय किया जाएगा। **The last date for submitting the completed applications by email is 10/06/2026 by 5.00 p.m.**

कार्यवाहक प्रमुख (आईआरडी स्थापना)

वितरण

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- Prof. Rahul Mishra, PI, C.A.R.E. :
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